

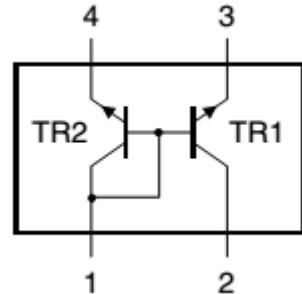


迈拓电子
MAITUO ELECTRONIC

BCV61 NPN General-purpose Double Transistor

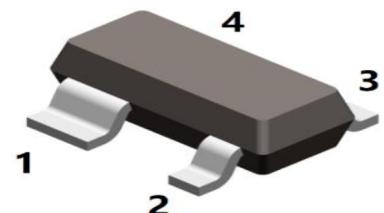
Features

- Low Current.
- Low Voltage.
- Matched Pairs.



Applications

- Applications With Working Point Independent of Temperature.
- Current Mirrors.



SOT-143

Ordering Information

Part Number	Package	Shipping	Marking Code
BCV61	SOT-143	3000 pcs / Tape & Reel	1M
BCV61A	SOT-143	3000 pcs / Tape & Reel	1J
BCV61B	SOT-143	3000 pcs / Tape & Reel	1K
BCV61C	SOT-143	3000 pcs / Tape & Reel	1L

Maximum Ratings (@T_A=25°C unless otherwise specified)

Symbol	Parameter	Value	Units
MAXIMUM RATINGS			
V _{CBO}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current - Continuous	0.1	A
I _{CM}	Collector Current – Peak	0.2	A
THERMAL CHARACTERISTIC			
P _{tot}	Total Power Dissipation, T _a ≤25°C	250	mW
T _J	Junction Temperature	150	°C
T _j , T _{stg}	Junction and Storage Temperature	-65 to +150	°C
R _{th (j-a)} (Note 1)	Thermal resistance from junction to ambient	500	°C/W



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Electrical Characteristics (@ $T_A=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	30	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	6	-	-	V
RCollector Cut-Off Current	I_{CBO}	$V_{CB} = 30V, I_E = 0$	-	-	15	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	-	-	100	nA
DC Current Gain ^(Note 1)	h_{FE}	$V_{CE} = 5V, I_C = 100\mu A$	100	-	-	
		$V_{CE} = 5V, I_C = 2mA$				
		BCV61	110		800	
		BCV61A	110		220	
		BCV61B	200		450	
		BCV61C	420		800	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 0.5mA$ $I_C = 100mA, I_B = 5mA$	- -	0.09 0.2	0.25 0.6	V
Base-Emitter Saturation Voltage ^(Note 2)	$V_{BE(sat)}$	$I_C = 10mA, I_B = 0.5mA$ $I_C = 100mA, I_B = 5mA$	- -	0.7 0.9	-	V
Base-Emitter Turn-on Voltage ^(Note 3)	$V_{BE(on)}$	$I_C = 2mA, V_{CE} = 5V$ $I_C = 10mA, V_{CE} = 5V$	0.58 -	0.66 -	0.7 0.77	V
Transition Frequency	f_T	$V_{CE} = 5V, I_C = 10mA,$ $f = 100MHz$	100	-	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	-	2.5	-	pF

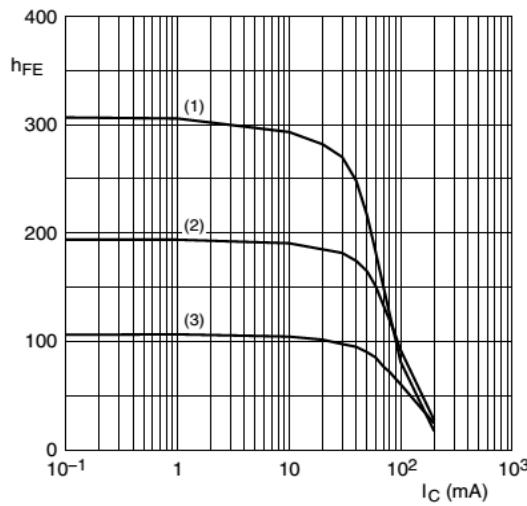
Notes:

- 1: Device mounted on an FR4 PCB.
- 2: V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
- 3: V_{BE} decreases by about 2 mV/K with increasing temperature.



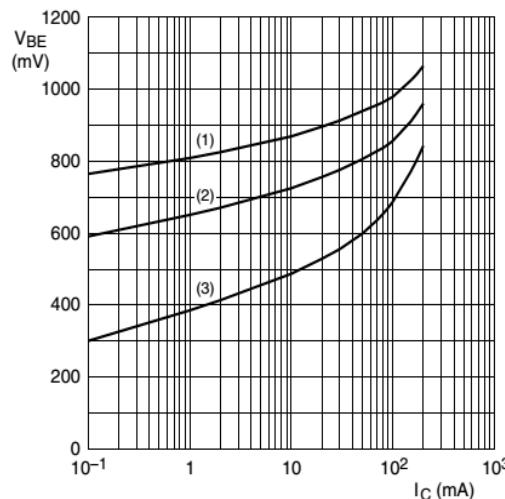
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Ratings and Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)



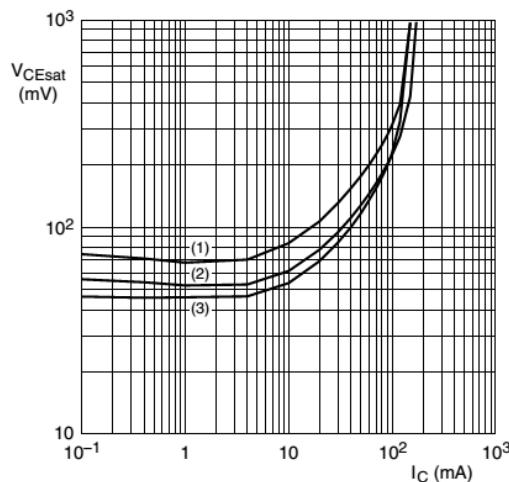
- $V_{CE} = 5 \text{ V}$
(1) $T_{amb} = 150^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig 1. BCV61A: DC current gain as a function of collector current; typical values



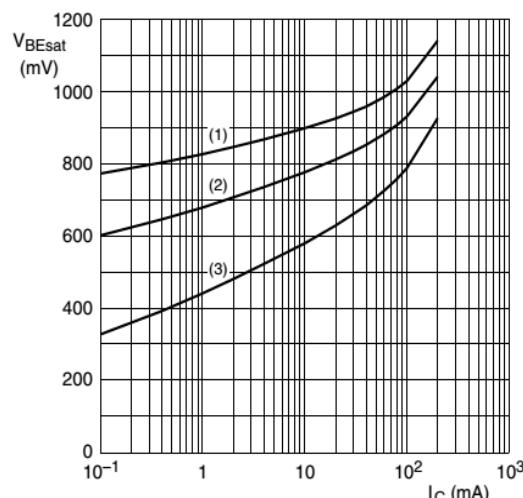
- $V_{CE} = 5 \text{ V}$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

Fig 2. BCV61A: Base-emitter voltage as a function of collector current; typical values



- $I_C/I_B = 20$
(1) $T_{amb} = 150^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig 3. BCV61A: Collector-emitter saturation voltage as a function of collector current; typical values

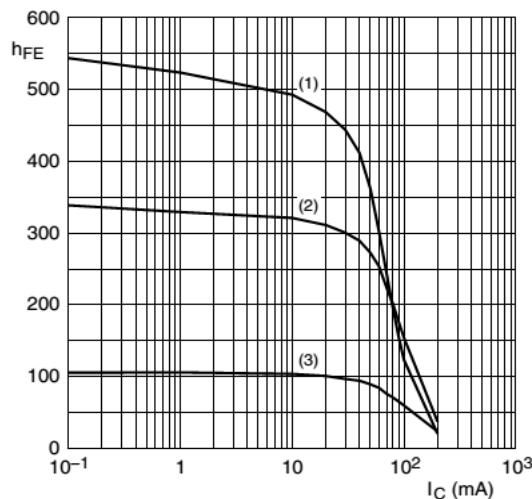


- $I_C/I_B = 10$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

Fig 4. BCV61A: Base-emitter saturation voltage as a function of collector current; typical values

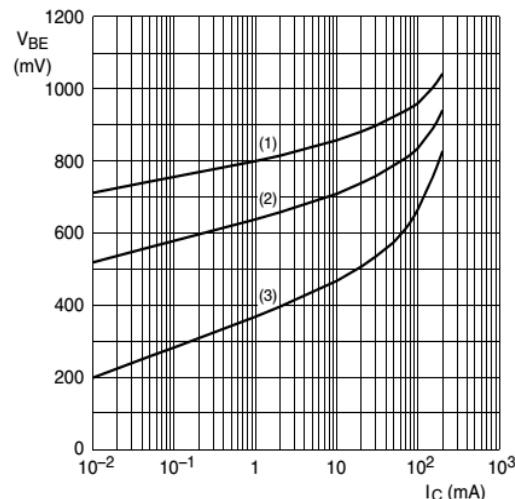


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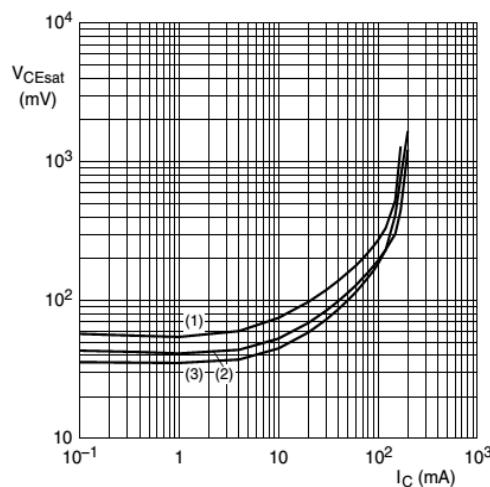
- $V_{CE} = 5\text{ V}$
(1) $T_{amb} = 150^\circ C$
(2) $T_{amb} = 25^\circ C$
(3) $T_{amb} = -55^\circ C$

Fig 5. BCV61B: DC current gain as a function of collector current; typical values



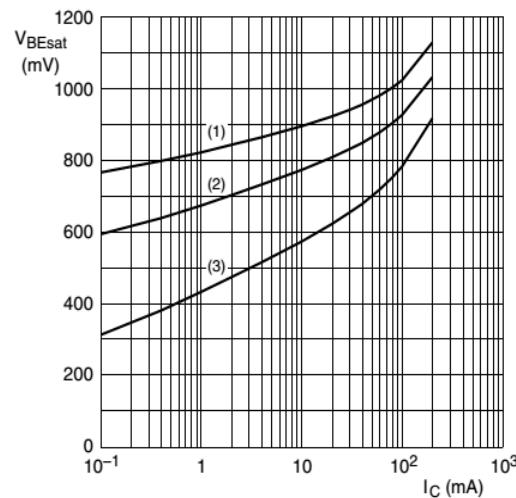
- $V_{CE} = 5\text{ V}$
(1) $T_{amb} = -55^\circ C$
(2) $T_{amb} = 25^\circ C$
(3) $T_{amb} = 150^\circ C$

Fig 6. BCV61B: Base-emitter voltage as a function of collector current; typical values



- $I_C/I_B = 20$
(1) $T_{amb} = 150^\circ C$
(2) $T_{amb} = 25^\circ C$
(3) $T_{amb} = -55^\circ C$

Fig 7. BCV61B: Collector-emitter saturation voltage as a function of collector current; typical values

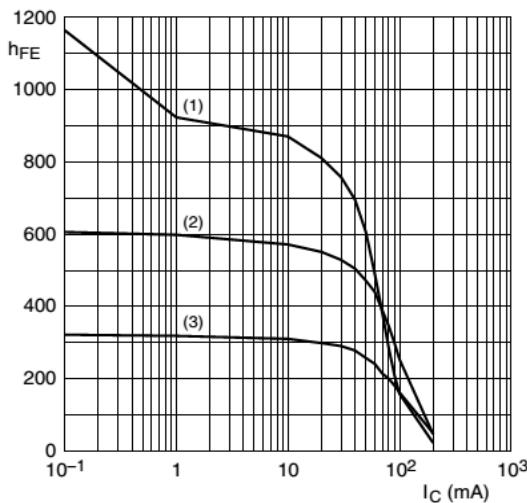


- $I_C/I_B = 10$
(1) $T_{amb} = -55^\circ C$
(2) $T_{amb} = 25^\circ C$
(3) $T_{amb} = 150^\circ C$

Fig 8. BCV61B: Base-emitter saturation voltage as a function of collector current; typical values

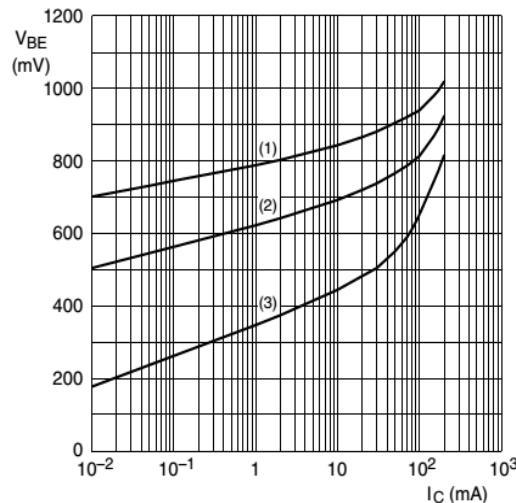


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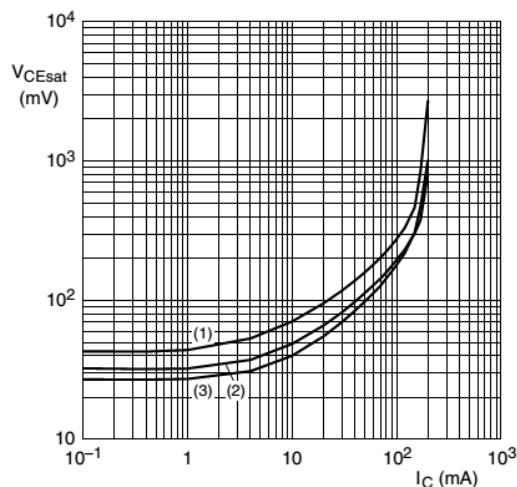
$V_{CE} = 5$ V
(1) $T_{amb} = 150$ °C
(2) $T_{amb} = 25$ °C
(3) $T_{amb} = -55$ °C

Fig 9. BCV61C: DC current gain as a function of collector current; typical values



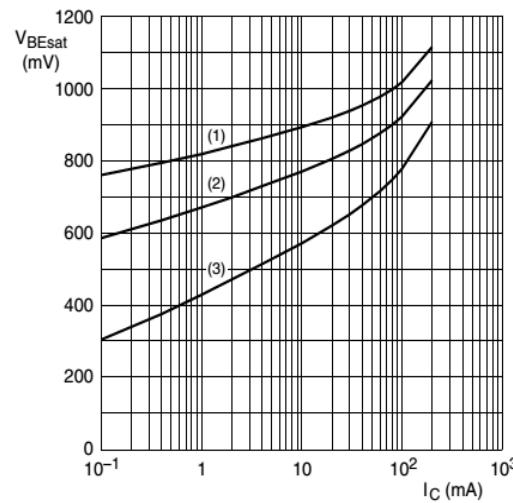
$V_{CE} = 5$ V
(1) $T_{amb} = -55$ °C
(2) $T_{amb} = 25$ °C
(3) $T_{amb} = 150$ °C

Fig 10. BCV61C: Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$
(1) $T_{amb} = 150$ °C
(2) $T_{amb} = 25$ °C
(3) $T_{amb} = -55$ °C

Fig 11. BCV61C: Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 10$
(1) $T_{amb} = -55$ °C
(2) $T_{amb} = 25$ °C
(3) $T_{amb} = 150$ °C

Fig 12. BCV61C: Base-emitter saturation voltage as a function of collector current; typical values



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Package Outline

Plastic surface mounted package

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DIM ^N	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.110	.120	2.80	3.04	—
B	.047	.055	1.20	1.40	—
C	.031	.047	.80	1.20	—
D	.014	.018	.37	.510	—
E	.030	.035	.76	.940	—
G	.076	BSC	1.92	BSC	—
H	.068	BSC	1.72	BSC	—
J	.003	.005	.085	.180	—
K	.002	.005	.013	.010	—
L	.010	.022	—	.55	REF
S	.082	.104	2.10	2.64	—